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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/768,944	01/30/2004	Muhammad Asif Khan	SETI-0001DIV	8944
23550 7590 06/26/2007 HOFFMAN WARNICK & D'ALESSANDRO, LLC 75 STATE STREET			EXAMINER	
			ERDEM, FAZLI	
	14TH FLOOR ALBANY, NY 12207		ART UNIT	PAPER NUMBER
112211111,111		·	2826	
			MAIL DATE	DELIVERY MODE
			06/26/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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		Application No.	Applicant(s)		
Office Action Summary		10/768,944	KHAN ET AL.		
		Examiner	Art Unit		
		Fazli Erdem	2826		
Period fo	The MAILING DATE of this communication apports Reply	pears on the cover sheet with the c	orrespondence address		
WHIC - Exte after - if NC - Failu Any	IORTENED STATUTORY PERIOD FOR REPL' CHEVER IS LONGER, FROM THE MAILING D. Insions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. O period for reply is specified above, the maximum statutory period of the toreply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing led patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tir will apply and will expire SIX (6) MONTHS from a, cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).		
Status					
• •	Responsive to communication(s) filed on <u>22 Jac</u> This action is FINAL . 2b) This Since this application is in condition for allowa closed in accordance with the practice under E	s action is non-final. nce except for formal matters, pr			
Disposit	ion of Claims				
5)⊠ 6)⊠ 7)□	Claim(s) <u>20-36</u> is/are pending in the application 4a) Of the above claim(s) is/are withdray Claim(s) <u>24-30,35 and 36</u> is/are allowed. Claim(s) <u>20-23 and 31-34</u> is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and/or	wn from consideration.			
Applicat	ion Papers				
10)	The specification is objected to by the Examine The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Examine The specification is objected to be specification in the specification in the specification is objected to be specification in the specification in the specification is objected to be specification in the specification in the specification is objected to be specification in the specification in the specification is objected to be specification in the specification in the specification is objected to be specification in the specification in the specification is objected to be specification in the specification in	cepted or b) objected to by the drawing(s) be held in abeyance. Se tion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ojected to. See 37 CFR 1.121(d).		
Priority	under 35 U.S.C. § 119				
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 					
2) Notice 3) Infor	nt(s) ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948) rmation Disclosure Statement(s) (PTO/SB/08) er No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal I 6) Other:	ate		

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DETAILED ACTION

Allowable Subject Matter

- 1. Claims 24-30, 35 and 36 allowed.
- 2. The following is a statement of reasons for the indication of allowable subject matter:

 Prior art failed to establish a nitride based heterostructure with a stack of buffer layer followed

 by GaN/AlGaN/InAlGaN on top of an insulating layer.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 4. Claims 20-23 and 31-34 rejected under 35 U.S.C. 102(b) as being anticipated by Masayuki (JP 09-27639).

Regarding Claim 20, Masayuki discloses a nitride based heterostructure device comprising: a substrate100, a buffer layer 101 directly on the substrate, wherein the buffer layer includes In; and a quaternary layer 102 directly on the buffer layer, wherein the quaternary layer includes Ga, AI, N, and In.

Regarding Claim 21, the device of claim 20, wherein the substrate comprises sapphire.

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Regarding Claim 22, the device of claim 20, wherein the quaternary layer 102 includes about a 20% to 30% molar fraction of A1.

Regarding Claim 23, the device of claim 22, wherein the quaternary layer further includes about a 2% to 5% molar fraction of In.

Regarding Claim 31, wherein the buffer layer 101 comprises a semi-insulating layer.

Regarding Claim 32, the device of claim 20, wherein the substrate 100 comprises a substantially nonconductive substrate.

Regarding Claim 33, nitride based heterostructure device comprising: a substrate 100; a buffer layer 101 on the substrate, wherein the buffer layer includes In; and a quaternary layer 102 on the buffer layer, wherein the quaternary layer includes Ga, A1, N, and In, wherein the quaternary layer includes about a 20% to 30% molar fraction of Al.

Regarding Claim 34, the device of claim 33, wherein the quaternary layer 101 further includes about a 2% to 5% molar fraction of In

Conclusion

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The examiner can normally be reached on M - F 8:00 - 5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Sue Purvis can be reached on (571) 272-1236. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

FE June 18, 2007

SUE A PUHVIS